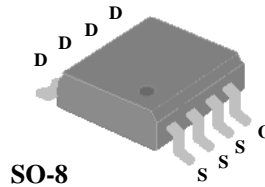
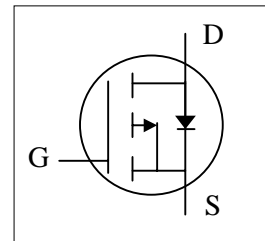


- ▼ Simple Drive Requirement
- ▼ Low On-resistance
- ▼ Fast Switching Characteristic
- ▼ RoHS Compliant & Halogen-Free



BV_{DSS}	-30V
$R_{DS(ON)}$	13.5m Ω
I_D	-11.3A



Description

XP4459 series are innovated design and silicon process technology to achieve the lowest possible on-resistance and fast switching performance. It provides the designer with an extreme efficient device for use in a wide range of power applications.

The SO-8 package is widely preferred for all commercial-industrial surface mount applications using infrared reflow technique and suited for voltage conversion or switch applications.

Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	-30	V
V_{GS}	Gate-Source Voltage	± 20	V
$I_D@T_A=25^\circ C$	Drain Current, $V_{GS} @ 10V^3$	-11.3	A
$I_D@T_A=70^\circ C$	Drain Current, $V_{GS} @ 10V^3$	-9	A
I_{DM}	Pulsed Drain Current ¹	-40	A
$P_D@T_A=25^\circ C$	Total Power Dissipation	2.5	W
T_{STG}	Storage Temperature Range	-55 to 150	$^\circ C$
T_J	Operating Junction Temperature Range	-55 to 150	$^\circ C$

Thermal Data

Symbol	Parameter	Value	Unit
Rthj-a	Maximum Thermal Resistance, Junction-ambient ³	50	$^\circ C/W$

Electrical Characteristics @ $T_j=25^\circ\text{C}$ (unless otherwise specified)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS}=0V, I_D=-250\mu A$	-30	-	-	V
$R_{DS(ON)}$	Static Drain-Source On-Resistance ²	$V_{GS}=-10V, I_D=-10A$	-	-	13.5	$m\Omega$
		$V_{GS}=-4.5V, I_D=-6A$	-	-	24	$m\Omega$
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS}=V_{GS}, I_D=-250\mu A$	-1	-	-3	V
g_{fs}	Forward Transconductance	$V_{DS}=-10V, I_D=-10A$	-	26	-	S
I_{DSS}	Drain-Source Leakage Current	$V_{DS}=-24V, V_{GS}=0V$	-	-	-10	μA
I_{GSS}	Gate-Source Leakage	$V_{GS}=\pm 20V, V_{DS}=0V$	-	-	± 0.1	μA
$Q_g(10V)$	Total Gate Charge	$I_D=-10A$ $V_{DS}=-15V$	-	40	64	nC
$Q_g(4.5V)$	Total Gate Charge		-	20	32	nC
Q_{gs}	Gate-Source Charge		-	7	-	nC
Q_{gd}	Gate-Drain ("Miller") Charge		-	8	-	nC
$t_{d(on)}$	Turn-on Delay Time	$V_{DS}=-15V$	-	12	-	ns
t_r	Rise Time	$I_D=-1A$	-	11	-	ns
$t_{d(off)}$	Turn-off Delay Time	$R_G=3.3\Omega$	-	85	-	ns
t_f	Fall Time	$V_{GS}=-10V$	-	47	-	ns
C_{iss}	Input Capacitance	$V_{GS}=0V$	-	2100	3360	pF
C_{oss}	Output Capacitance	$V_{DS}=-15V$	-	300	-	pF
C_{rss}	Reverse Transfer Capacitance	$f=1.0\text{MHz}$	-	250	-	pF
R_g	Gate Resistance	$f=1.0\text{MHz}$	-	10	20	Ω

Source-Drain Diode

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
V_{SD}	Forward On Voltage ²	$I_S=-2.1A, V_{GS}=0V$	-	-	-1.2	V
t_{rr}	Reverse Recovery Time	$I_S=-10A, V_{GS}=0V,$	-	16	-	ns
Q_{rr}	Reverse Recovery Charge	$dI/dt=100A/\mu s$	-	7	-	nC

Notes:

1. Pulse width limited by Max. junction temperature.
2. Pulse test
3. Surface mounted on 1 in² copper pad of FR4 board, $t \leq 10s$; 125 °C/W when mounted on Min. copper pad.

THIS PRODUCT IS SENSITIVE TO ELECTROSTATIC DISCHARGE, PLEASE HANDLE WITH CAUTION.

USE OF THIS PRODUCT AS A CRITICAL COMPONENT IN LIFE SUPPORT, AUTOMOTIVE OR OTHER SIMILAR SYSTEMS IS NOT AUTHORIZED.

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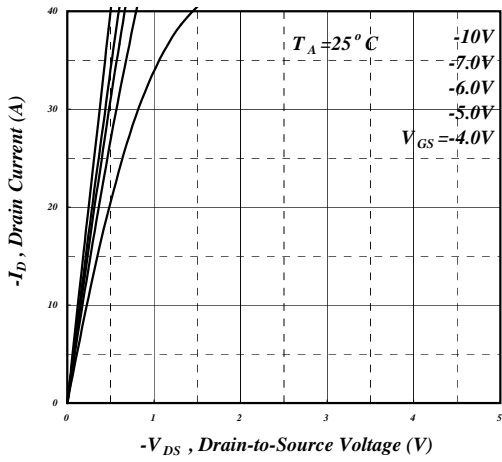


Fig 1. Typical Output Characteristics

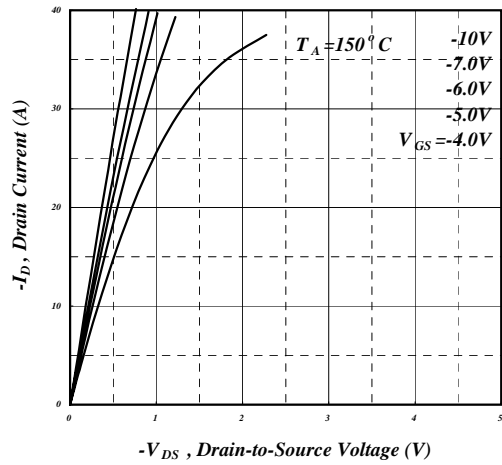


Fig 2. Typical Output Characteristics

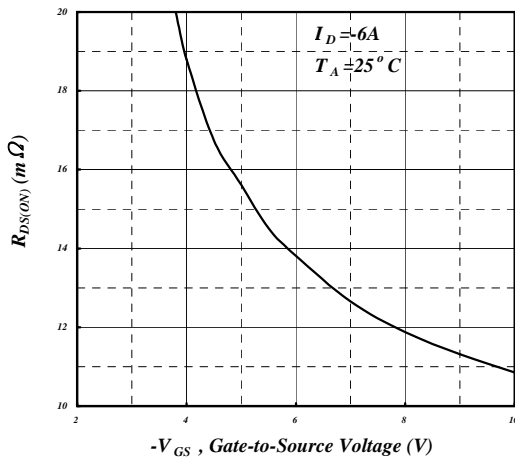


Fig 3. On-Resistance v.s. Gate Voltage

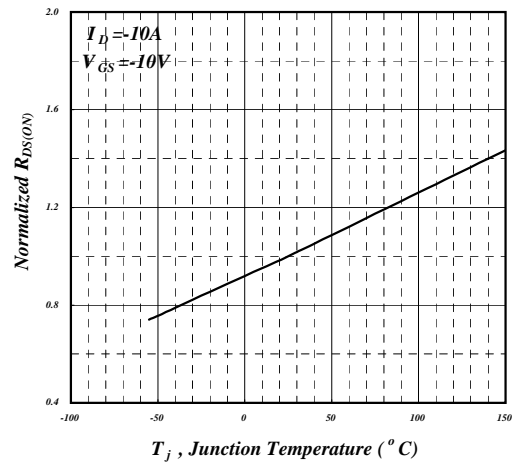


Fig 4. Normalized On-Resistance v.s. Junction Temperature

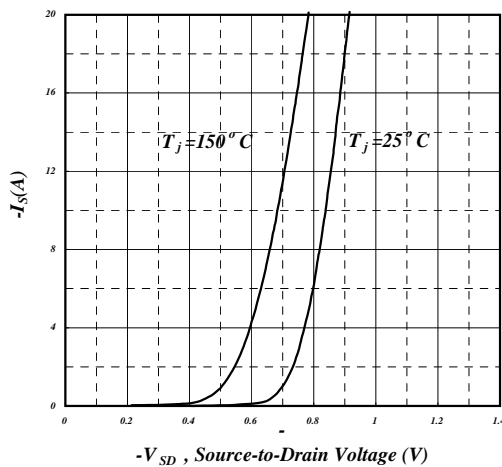


Fig 5. Forward Characteristic of Reverse Diode

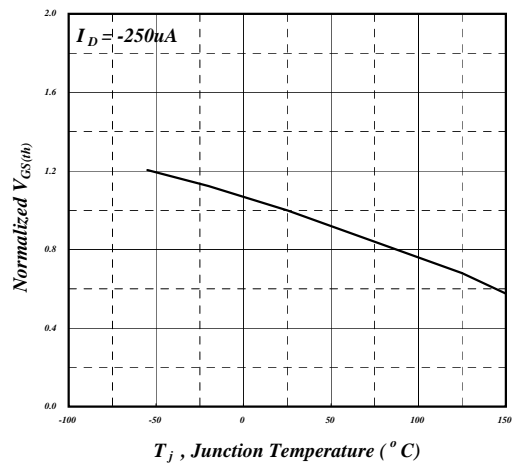


Fig 6. Gate Threshold Voltage v.s. Junction Temperature

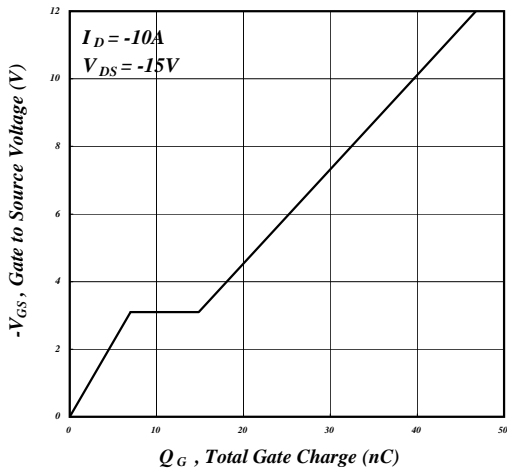


Fig 7. Gate Charge Characteristics

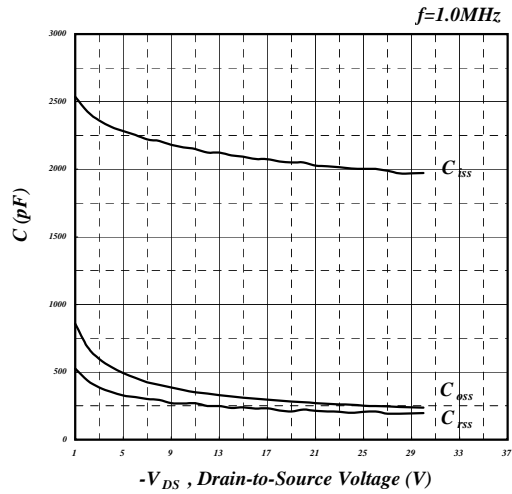


Fig 8. Typical Capacitance Characteristics

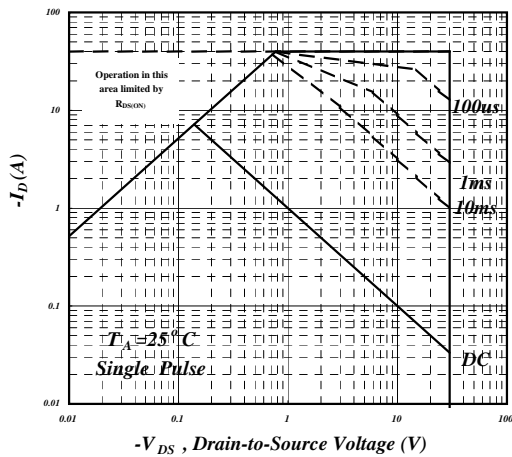


Fig 9. Maximum Safe Operating Area

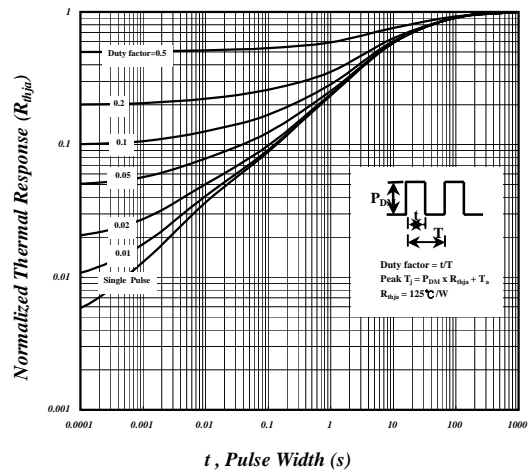


Fig 10. Effective Transient Thermal Impedance

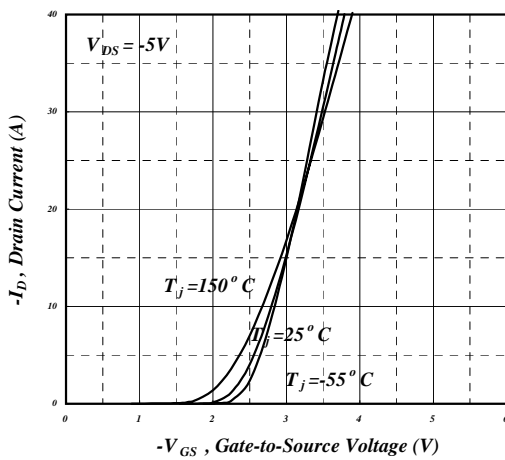


Fig 11. Transfer Characteristics

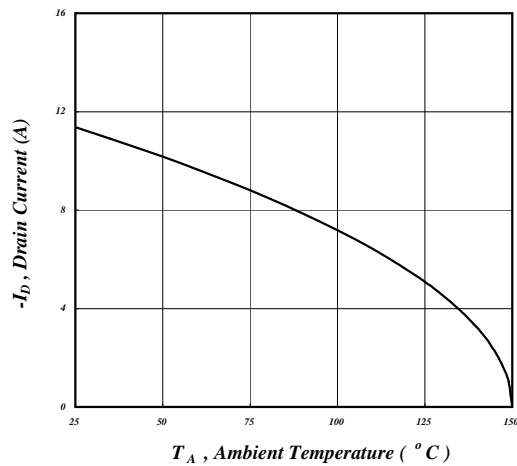


Fig 12. Drain Current v.s. Ambient Temperature

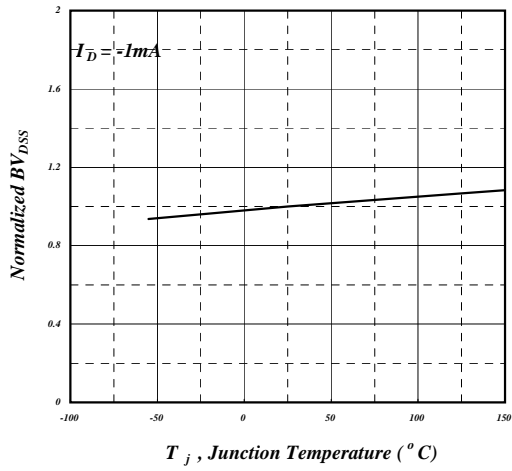


Fig 13. Normalized BV_{DSS} v.s. Junction Temperature

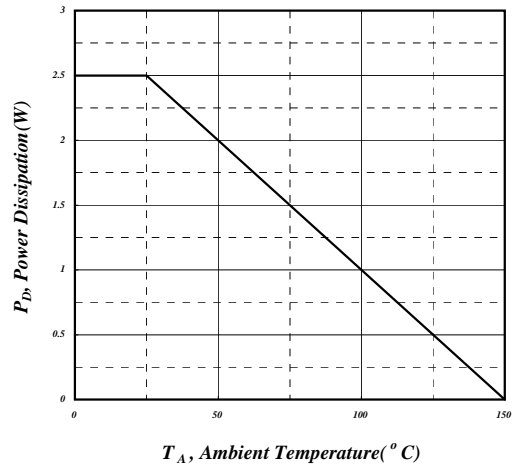


Fig 14. Total Power Dissipation

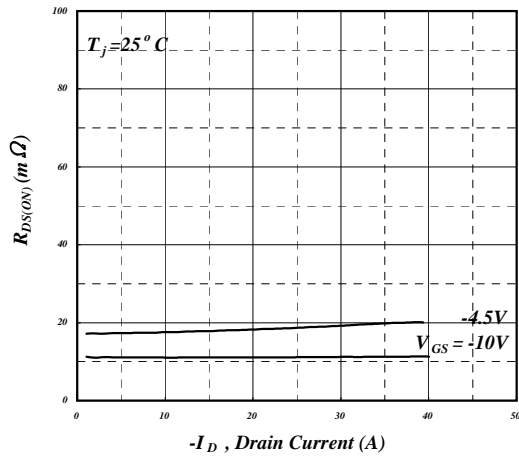
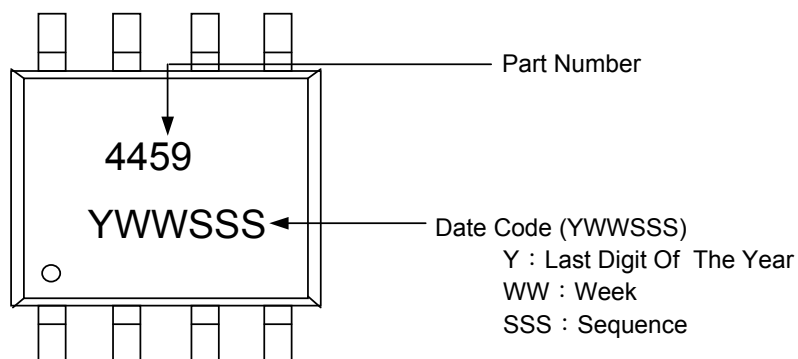
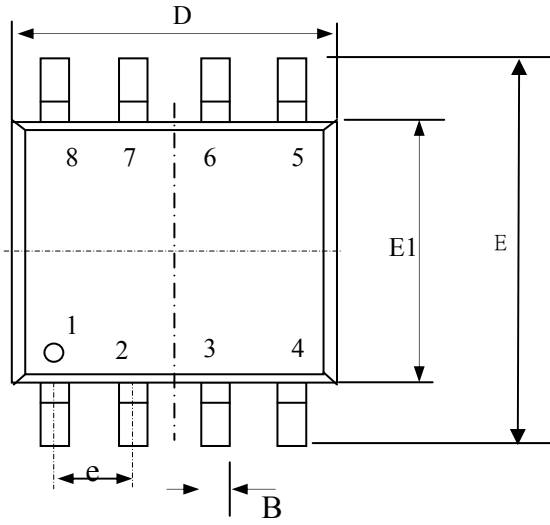


Fig 15. Typ. Drain-Source on State Resistance

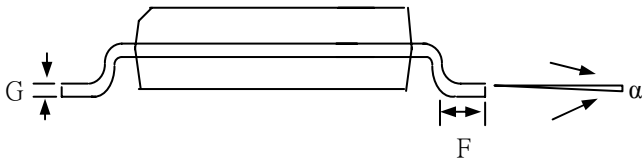
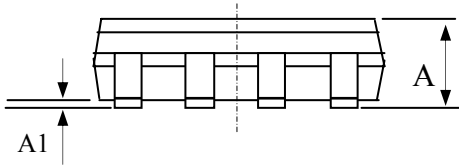
MARKING INFORMATION



Package Outline : SO-8



SYMBOLS	Millimeters		
	MIN	NOM	MAX
A	1.35	1.55	1.75
A1	0.05	0.15	0.25
B	0.30	0.41	0.51
D	4.80	5.05	5.30
E	5.79	6.00	6.20
E1	3.70	3.90	4.10
e	1.27 TYP		
G	0.17	0.21	0.25
F	0.38	0.83	1.27
α	0°	4°	8°



- 1.All Dimension Are In Millimeters.
- 2.Dimension Does Not Include Mold Protrusions.

SO-8 FOOTPRINT :

